



DMN2041L

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

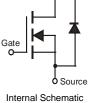
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

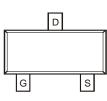
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)







Drain



TOP VIEW

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±12	V	
Continuous Drain Current (Note 3)Steady State $T_A = 25^{\circ}C$ $T_A = 70^{\circ}C$			I _D	6.4 4.5	A
Pulsed Drain Current (Note 4)			IDM	30	А

Thermal Characteristics

Notes:

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	0.78	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{0JA}	161	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

1. No purposefully added lead.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
Device mounted on FR-4 PCB with minimum recommended pad layout.

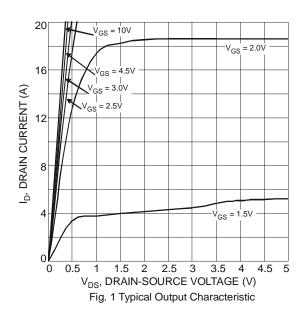
4. Repetitive rating, pulse width limited by junction temperature.

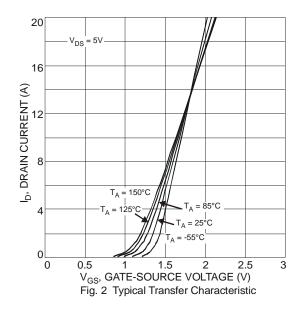


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Provin	_	20	28	mΩ	$V_{GS} = 4.5V, I_D = 6.0A$	
Static Drain-Source On-Resistance	R _{DS (ON)}		26	41	111 2 2	$V_{GS} = 2.5V, I_D = 5.2A$	
Forward Transfer Admittance	Y _{fs}	-	6	-	S	$V_{DS} = 10V, I_D = 6A$	
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	550	-			
Output Capacitance	C _{oss}	-	88	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	81	-			
Gate Resistance	R _g	-	1.34	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (10V)	Qg	-	15.6	-	nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$	
Total Gate Charge (4.5V)	Qg	-	7.2	-			
Gate-Source Charge	Q _{gs}	-	1.0	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_{D} = 6A$	
Gate-Drain Charge	Q _{gd}	-	1.9	-			
Turn-On Delay Time	t _{D(on)}	-	4.69	-			
Turn-On Rise Time	tr	-	13.19	-]	$V_{DD} = 10V, V_{GEN} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	22.10	-	ns	$R_{GEN} = 1\Omega$, $I_D = 6.7A$	
Turn-Off Fall Time	t _f	-	6.43	-]		

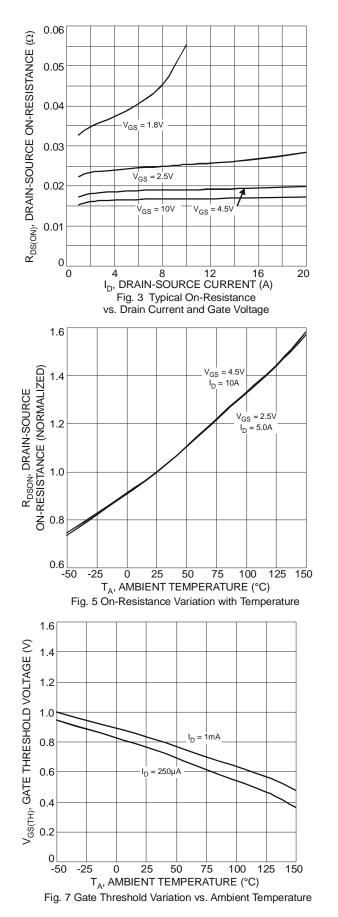
Notes: 5. Short duration pulse test used to minimize self-heating effect. 6. Guaranteed by design. Not subject to production testing.

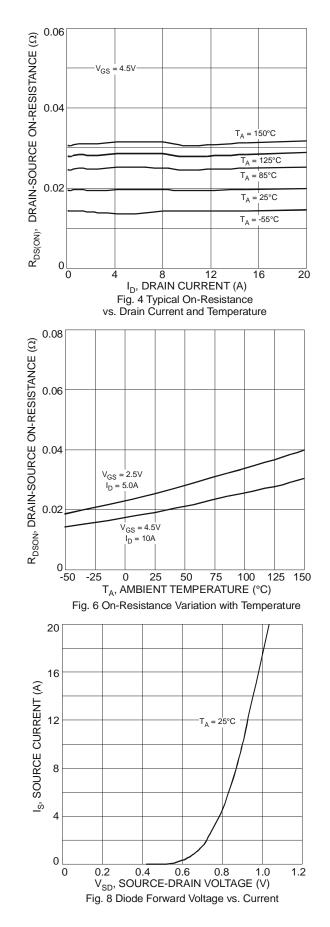




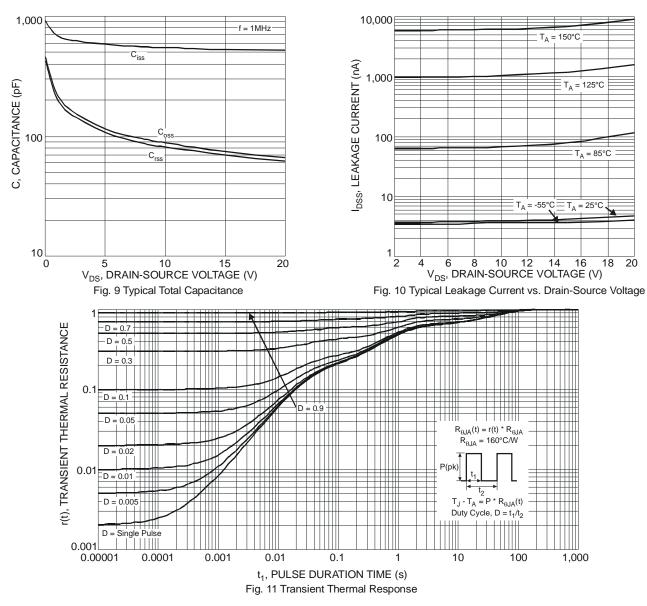


NEW PRODUCT







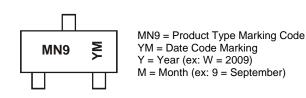


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN2041L-7	SOT-23	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

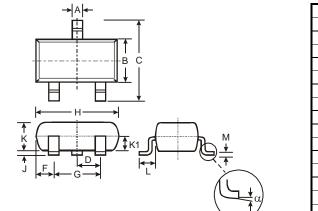


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Date Code Key												
Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Y	Z	7	А		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

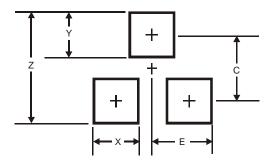


Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
Κ	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

NEW PRODUCT



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